NSN 5961-01-295-5038

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View Online at https://aerobasegroup.com/nsn/5961-01-295-5038 **Inclosure Material:** Metal all transistor **Overall Length:** 0.210 inches all transistor **Terminal Length:** 1.500 inches all transistor **Overall Diameter:** 0.230 inches all transistor **Internal Configuration:** Field effect all transistor **Channel Polarity And Control Type (non-core):** N-channel insulated gate type all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Terminal all transistor **Terminal Circle Diameter:** 0.100 inches all transistor **Features Provided:** Burn in and electrostatic sensitive and hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 20.0 drain to source voltage all transistor and 20.0 drain to gate voltage all transistor and -20.0 gate to source voltage all transistor **Current Rating Per Characteristic:** 50.00 milliamperes zero-gate-voltage source current horsepower metric all transistor **Power Rating Per Characteristic:** 400.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 4 uninsulated wire lead all transistor **Specification Data:** 95105-204-0016-020 manufacturers specification control Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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